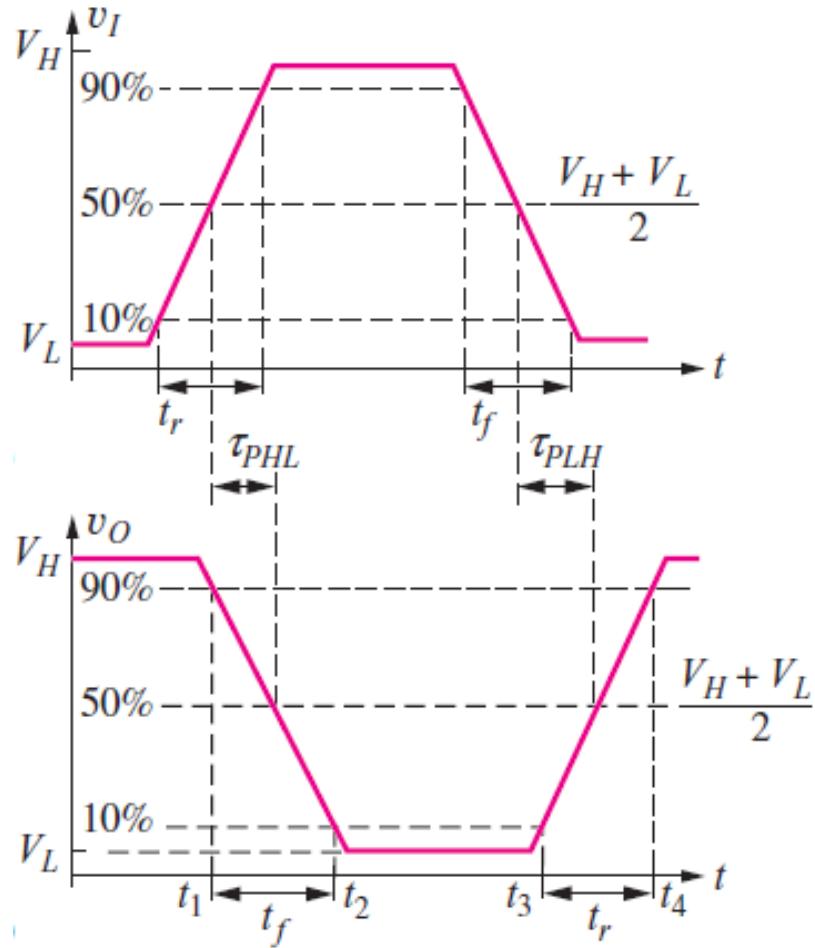


Announcements

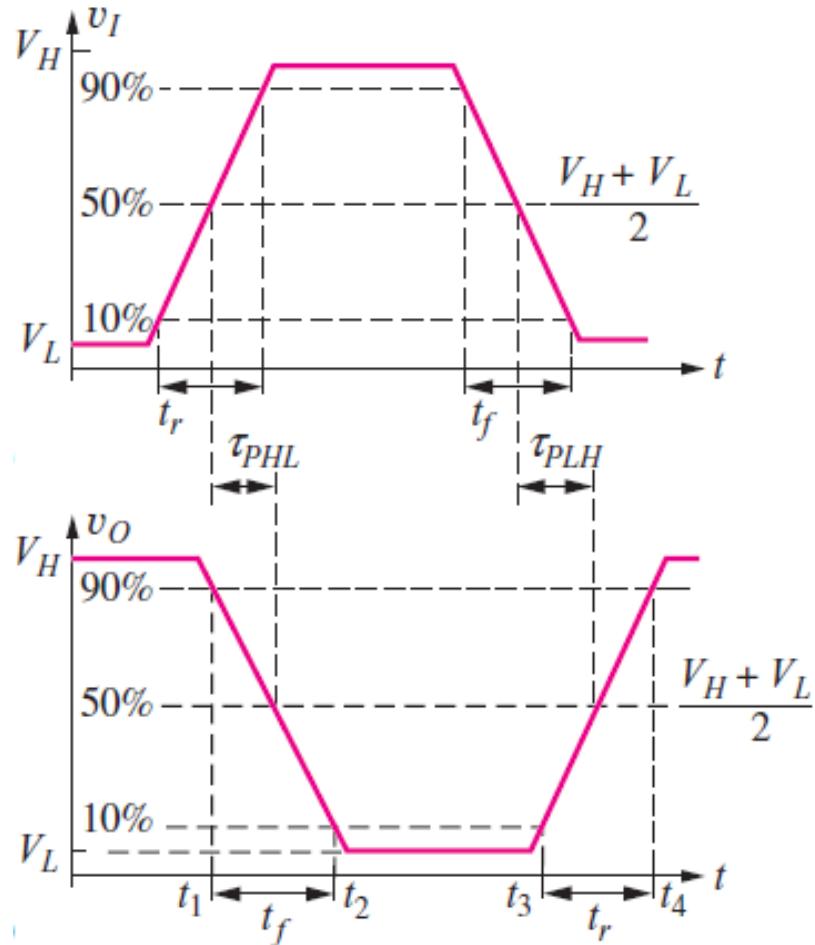
- Homework 7 due Friday in class.
- Exam 2 being graded.
- Final project to be posted tonight.
 - XOR/LED as posted, but with some tweaks to specs, etc.

Logic Gate Dynamic Responses



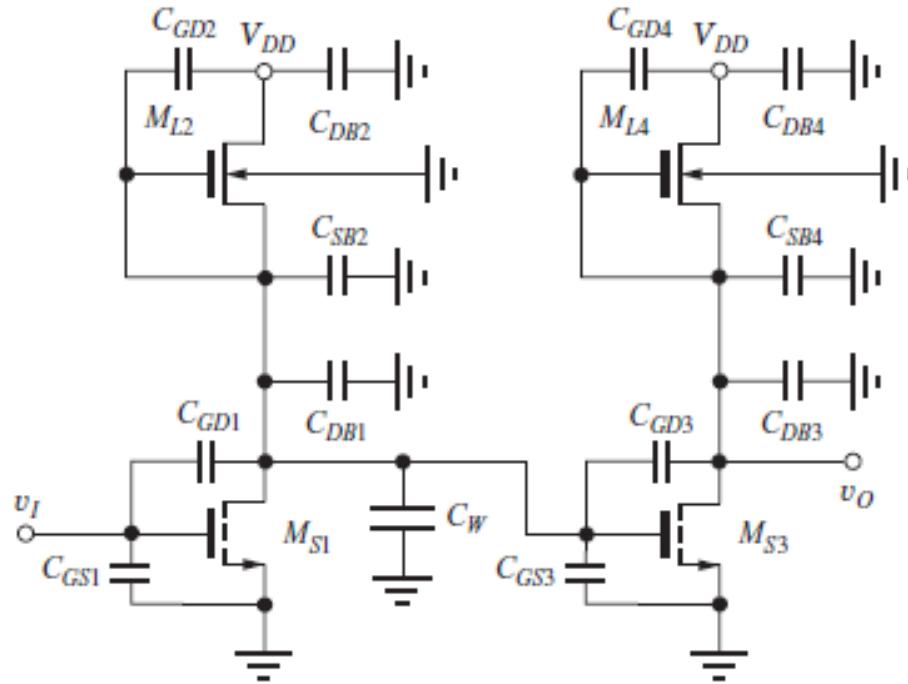
- **Logic Swing:**
$$\Delta V = V_H - V_L$$
- **10 percent point:**
$$V_{10\%} = V_L + 0.1 \Delta V$$
- **90 percent point:**
$$V_{90\%} = V_L + 0.9 \Delta V$$
- **50 percent point:**
$$V_{50\%} = (V_L + V_H)/2$$

Logic Gate Dynamic Responses

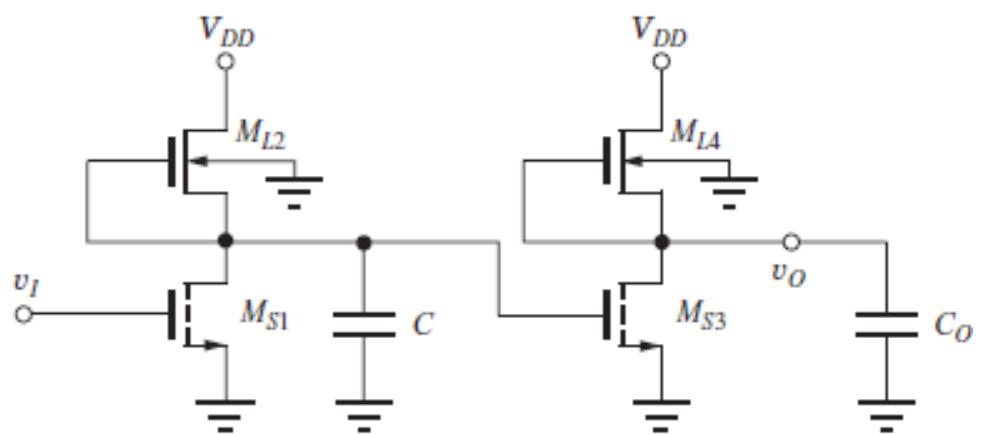


- **Rise time (t_r):** time required from 10% point to 90% point
- **Fall time (t_f):** time required from 90% point to 10% point
- **Propagation delay (τ_p):** difference in time between the input and output signals reaching the 50% points
 - for output high-to-low: τ_{PHL}
 - for output low-to-high: τ_{PLH}
 - average propagation delay $\tau_p = (\tau_{PLH} + \tau_{PHL})/2$

Capacitances in Logic Circuits

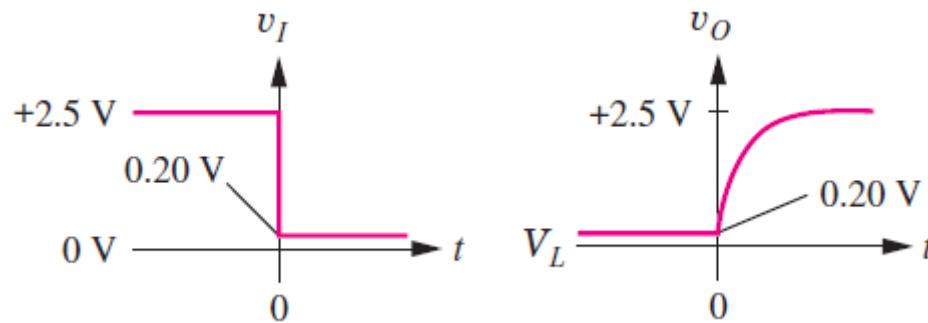
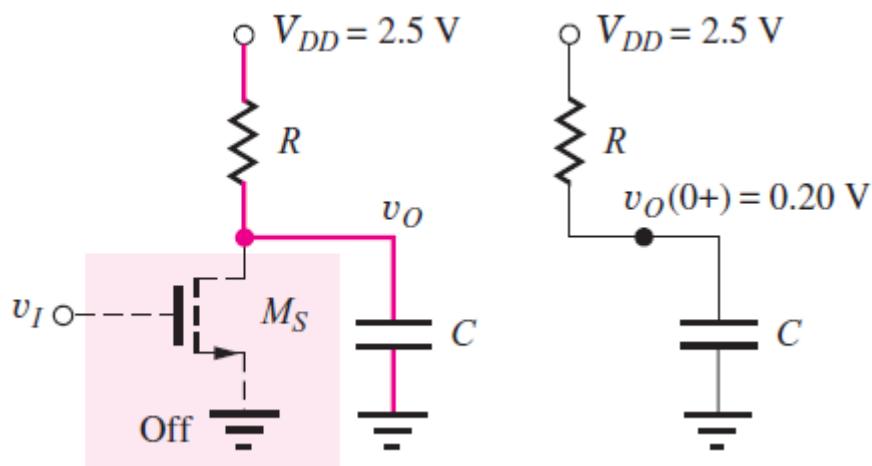


Various capacitances
associated with transistors



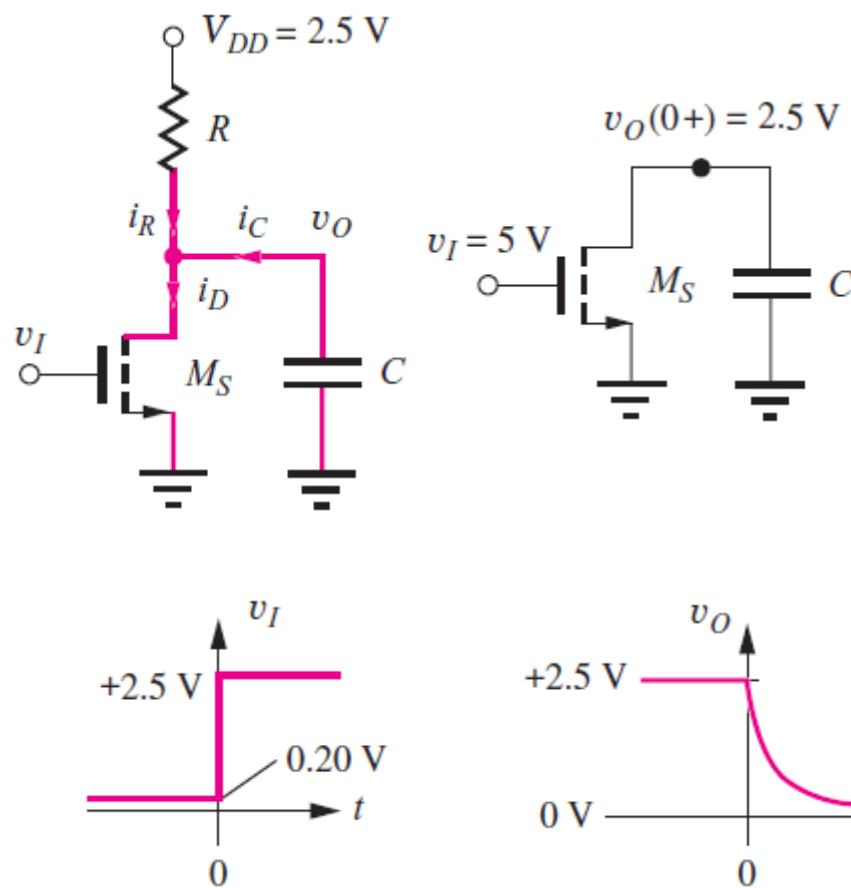
The capacitances on a given node can be lumped into a fixed effective nodal capacitance C

Dynamic Response of NMOS Resistive Load Inverter



- Assume abrupt V_I change from V_H to V_L
- V_O changes from V_L to V_H by **charging C via R**
- From RC circuit basics
$$t_r = 2.2 RC$$
$$\tau_{PLH} = 0.69 RC$$

Dynamic Response of NMOS Resistive Load Inverter



- Assume abrupt V_I change from V_L to V_H
- V_O changes from V_H to V_L by **discharging C via M_S**
- R_{on} of M_S changes with time
=> use an effective resistance
$$R_{\text{eff}} = 1.7 R_{\text{ons}}$$

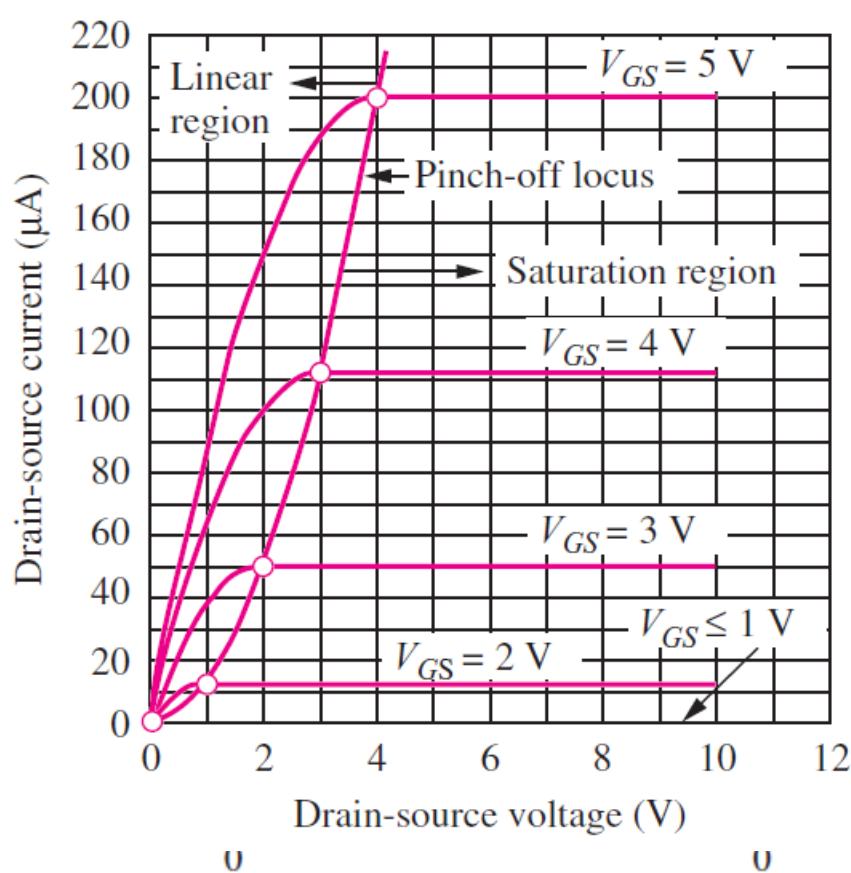
where $R_{\text{ons}} = [K_n(V_H - V_{TNS})]^{-1}$

- From RC circuit basics

$$t_f = 2.2 R_{\text{eff}} C = 3.7 R_{\text{ons}} C$$

$$\tau_{PHL} = 0.69 R_{\text{eff}} C = 1.2 R_{\text{ons}} C$$

Dynamic Response of NMOS Resistive Load Inverter



- Assume abrupt V_i change from V_L to V_H
- V_o changes from V_H to V_L by **discharging C via M_S**
- R_{on} of M_S changes with time
=> use an effective resistance

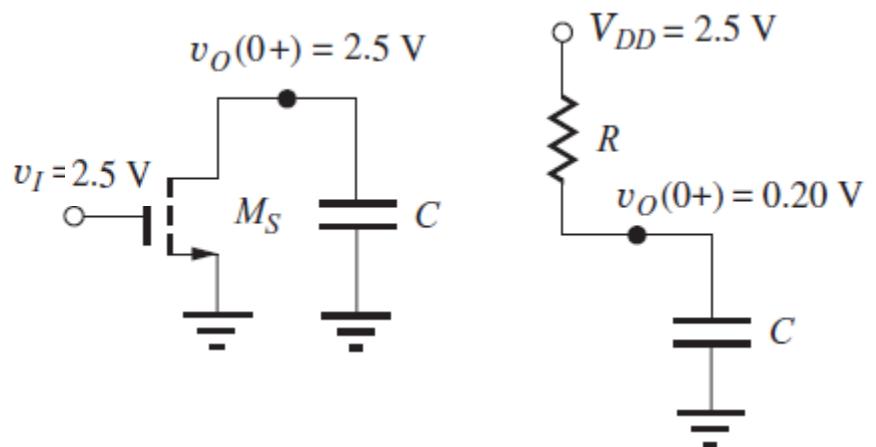
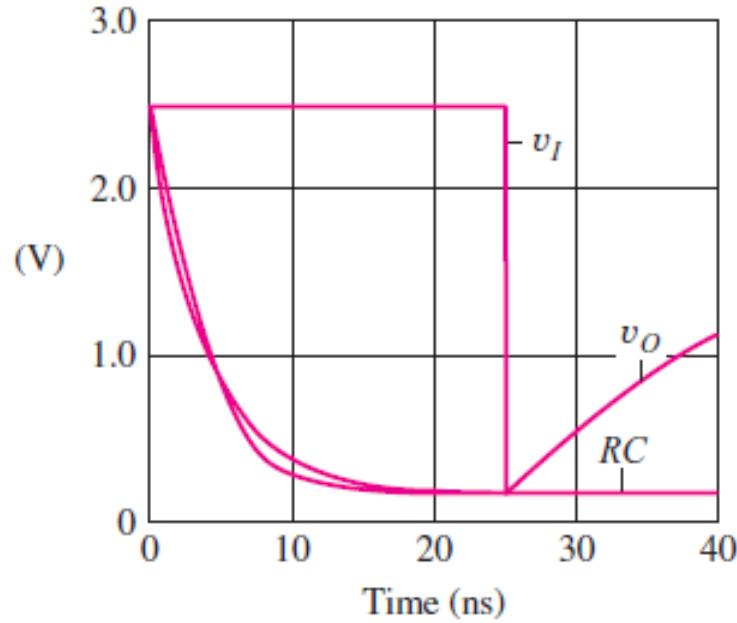
$$R_{\text{eff}} = 1.7 R_{\text{on}_S}$$

where $R_{\text{on}_S} = [K_n(V_H - V_{TNS})]^{-1}$

- From RC circuit basics
- $$t_f = 2.2 R_{\text{eff}} C = 3.7 R_{\text{on}_S} C$$
- $$\tau_{PHL} = 0.69 R_{\text{eff}} C = 1.2 R_{\text{on}_S} C$$

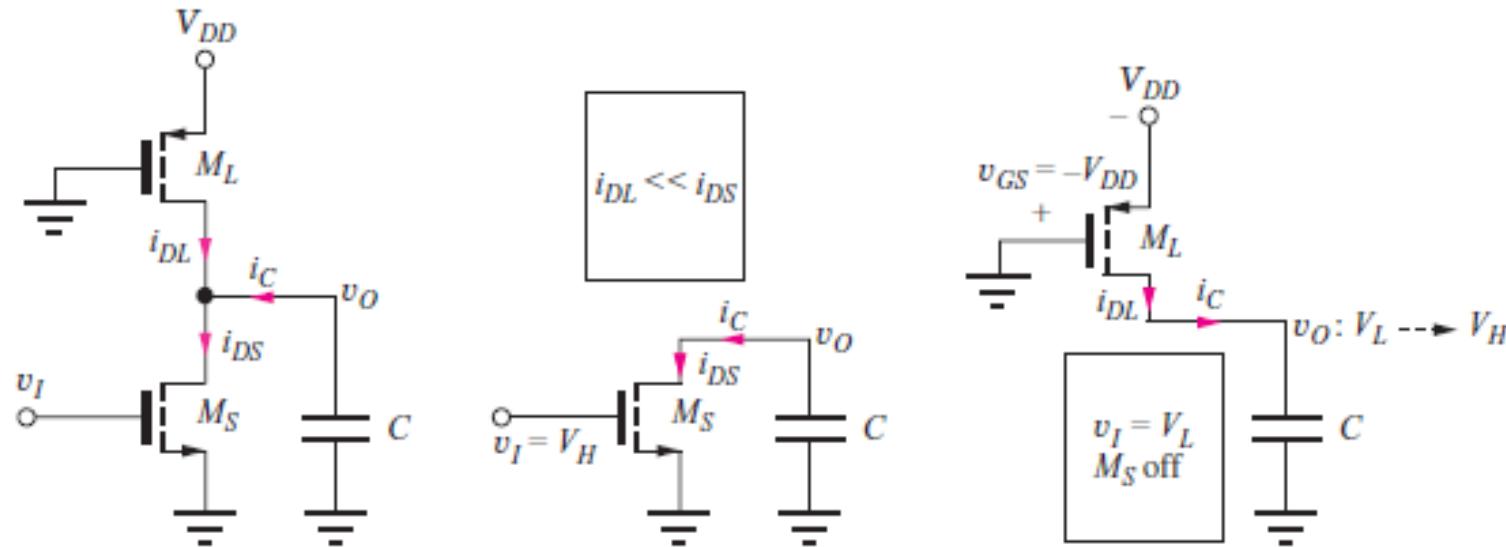
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Dynamic Response of NMOS Resistive Load Inverter



- Note the asymmetry in τ_{PLH} and τ_{PHL} ($\tau_{PHL} < \tau_{PLH}$)!
- Switching device must have a much smaller R_{on} than that of the load in order to produce the desired low logic level (V_L)

Dynamic Response of Inverters with Transistor Load Designs



- V_O changes from V_H to V_L by **discharging C via M_S**
- $t_f, \tau_{PHL} \propto R_{onS} C$
- V_O changes from V_L to V_H by **charging C via M_L**
- $t_r, \tau_{PLH} \propto R_{onL} C$, where $R_{onL} = (K_L |V_{GS} - V_{TNL}|)^{-1}$

NMOS Inverter Delays

TABLE 6.10
NMOS Inverter Time Delays

	τ_{PHL}	τ_{PLH}	t_f	t_r
Resistor load	$1.2R_{onS}C$	$0.69RC$	$3.7R_{onS}C$	$2.2RC$
Pseudo NMOS	$1.2R_{onS}C$	$1.2R_{onL}C$	$3.7R_{onS}C$	$3.7R_{onL}C$
Depletion load	$1.2R_{onS}C$	$3.6R_{onL}C$	$3.7R_{onS}C$	$8.1R_{onL}C$
Saturated load	$1.2R_{onS}C$	$3.0R_{onL}C$	$3.7R_{onS}C$	$11.9R_{onL}C$
Linear load	$1.2R_{onS}C$	$0.69R_{onL}C$	$3.7R_{onS}C$	$3.7R_{onL}C$

$$R_{onS} = \frac{1}{K_S(V_H - V_{TNS})}$$
$$R_{onL} = \frac{1}{K_L|V_{GS} - V_{TNL}|}$$

- t_f, τ_{PHL} are the same
- t_r, τ_{PLH} are different due to different current carrying capacity of load transistors

NMOS Performance Scaling

- $\tau_P = \frac{\tau_{PHL} + \tau_{PLH}}{2}$
 - $\tau_P \propto C$
 - $\tau_P \propto R_{on} \propto \left(\frac{W}{L}\right)^{-1}$

	τ_{PHL}	τ_{PLH}	t_f	t_r
Resistor load	$1.2R_{onS}C$	$0.69RC$	$3.7R_{onS}C$	$2.2RC$
Pseudo NMOS	$1.2R_{onS}C$	$1.2R_{onL}C$	$3.7R_{onS}C$	$3.7R_{onL}C$
Depletion load	$1.2R_{onS}C$	$3.6R_{onL}C$	$3.7R_{onS}C$	$8.1R_{onL}C$
Saturated load	$1.2R_{onS}C$	$3.0R_{onL}C$	$3.7R_{onS}C$	$11.9R_{onL}C$
Linear load	$1.2R_{onS}C$	$0.69R_{onL}C$	$3.7R_{onS}C$	$3.7R_{onL}C$

$$R_{onS} = \frac{1}{K_S(V_H - V_{TNS})}$$
$$R_{onL} = \frac{1}{K_L|V_{GS} - V_{TNL}|}$$

- Delay is proportional to total load capacitance C , and inversely proportional to W/L .
- Larger size (larger W/L) => shorter delay, but larger power (last lecture: power scaling)

Switching Speed in Logic Circuits

- Can estimate switching time for capacitive load very simply:

$$i = C \frac{dv}{dt} \rightarrow \Delta t = \frac{C_{\text{total}} \Delta v}{i_{\text{avg}}} = \frac{\Delta Q}{i_{\text{avg}}}$$

- Δv is voltage swing
- Estimate i_{avg} using trapezoidal rule: $i_{\text{avg}} = (i_{\text{init}} + i_{\text{final}})/2$
 - Can improve estimate by using $\Delta t = \Delta t_1 + \Delta t_2 + \dots$ associated with $\Delta v = \Delta v_1 + \Delta v_2 + \dots$

